



THE UNITED STATES PATENT AND TRADEMARK OFFICE

AF/2813
#P/Amend C
MS
Bref
3/21/02

In re Application of

Andrews et al.

Serial No.: 09/883,981

Group Art Unit: 2813

Filed: June 20, 2001

Examiner: D. Blum

For: LOW COST SHALLOW TRENCH ISOLATION USING NON-CONFORMAL
DIELECTRIC MATERIAL

Honorable Assistant Commissioner of Patents
Washington, D.C. 20231
Box AF

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AMENDMENT UNDER 37 C.F.R. §1.116

Sir:

In response to the Office Action dated January 17, 2002, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend the claims to read as follows:

23. (Twice Amended) A semiconductor substrate having a planarized structure formed according to a method comprising:
- forming a pad on a surface of said substrate;
 - forming at least one trench in said substrate;
 - applying a filler material by high density plasma method in said at least one trench and on said pad, said filler material filling at least a portion of said at least one trench;
 - selectively removing said filler material on said pad so as to separate said filler material in said at least one trench and said filler material on said surface by an exposed area of said pad, and
 - removing said filler material on said pad while allowing said filler material in said at least a portion of said at least one trench to remain.

OK to
DS-3
3/20/02